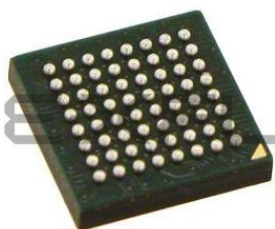


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Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I ² C, IrDA, SPI, UART/USART
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	44
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 19x16b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LFBGA
Supplier Device Package	64-MAPBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk10dx64vmp5

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Terminology and guidelines

Field	Description	Values
FFF	Program flash memory size	• 32 = 32 KB • 64 = 64 KB • 128 = 128 KB • 256 = 256 KB • 512 = 512 KB • 1M0 = 1 MB
R	Silicon revision	• Z = Initial • (Blank) = Main • A = Revision after main
T	Temperature range (°C)	• V = -40 to 105 • C = -40 to 85
PP	Package identifier	• FM = 32 QFN (5 mm x 5 mm) • FT = 48 QFN (7 mm x 7 mm) • LF = 48 LQFP (7 mm x 7 mm) • LH = 64 LQFP (10 mm x 10 mm) • MP = 64 MAPBGA (5 mm x 5 mm) • LK = 80 LQFP (12 mm x 12 mm) • MB = 81 MAPBGA (8 mm x 8 mm) • LL = 100 LQFP (14 mm x 14 mm) • ML = 104 MAPBGA (8 mm x 8 mm) • MC = 121 MAPBGA (8 mm x 8 mm) • LQ = 144 LQFP (20 mm x 20 mm) • MD = 144 MAPBGA (13 mm x 13 mm) • MJ = 256 MAPBGA (17 mm x 17 mm)
CC	Maximum CPU frequency (MHz)	• 5 = 50 MHz • 7 = 72 MHz • 10 = 100 MHz • 12 = 120 MHz • 15 = 150 MHz
N	Packaging type	• R = Tape and reel • (Blank) = Trays

2.4 Example

This is an example part number:

MK10DN128VLH5

3 Terminology and guidelines

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

3.1.1 Example

This is an example of an operating requirement, which you must meet for the accompanying operating behaviors to be guaranteed:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	0.9	1.1	V

3.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior, which is guaranteed if you meet the accompanying operating requirements:

Symbol	Description	Min.	Max.	Unit
I _{WP}	Digital I/O weak pullup/pulldown current	10	130	μA

3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

5.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} - V_{DDA}$	V_{DD} -to- V_{DDA} differential voltage	-0.1	0.1	V	
$V_{SS} - V_{SSA}$	V_{SS} -to- V_{SSA} differential voltage	-0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
V_{IH}	Input high voltage $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ $1.7\text{ V} \leq V_{DD} \leq 2.7\text{ V}$	$0.7 \times V_{DD}$	—	V	
		$0.75 \times V_{DD}$	—	V	
V_{IL}	Input low voltage $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ $1.7\text{ V} \leq V_{DD} \leq 2.7\text{ V}$	—	$0.35 \times V_{DD}$	V	
		—	$0.3 \times V_{DD}$	V	
V_{HYS}	Input hysteresis	$0.06 \times V_{DD}$	—	V	
I_{ICIO}	I/O pin DC injection current — single pin $V_{IN} < V_{SS}-0.3\text{V}$ (Negative current injection) $V_{IN} > V_{DD}+0.3\text{V}$ (Positive current injection)	-3 —	— +3	mA	1
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins - Negative current injection - Positive current injection	-25 —	— +25	mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is greater than V_{AIO_MIN} ($=V_{SS}-0.3\text{V}$) and V_{IN} is less than V_{AIO_MAX} ($=V_{DD}+0.3\text{V}$) is observed, then there is no need to provide current limiting resistors at the pads. If these limits cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO_MIN}-V_{IN})/|I_{IC}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO_MAX})/|I_{IC}|$. Select the larger of these two calculated resistances.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling V_{DD} POR detect voltage	0.8	1.1	1.5	V	

Table continues on the next page...

5.2.3 Voltage and current operating behaviors

Table 4. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — high drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OH} = -9\text{ mA}$	$V_{DD} - 0.5$	—	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OH} = -3\text{ mA}$	$V_{DD} - 0.5$	—	V	
	Output high voltage — low drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OH} = -2\text{ mA}$	$V_{DD} - 0.5$	—	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OH} = -0.6\text{ mA}$	$V_{DD} - 0.5$	—	V	
I_{OHT}	Output high current total for all ports	—	100	mA	
V_{OL}	Output low voltage — high drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OL} = 9\text{ mA}$	—	0.5	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OL} = 3\text{ mA}$	—	0.5	V	
	Output low voltage — low drive strength				
	• $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, $I_{OL} = 2\text{ mA}$	—	0.5	V	
	• $1.71\text{ V} \leq V_{DD} \leq 2.7\text{ V}$, $I_{OL} = 0.6\text{ mA}$	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	100	mA	
I_{IN}	Input leakage current (per pin)				
	• @ full temperature range	—	1.0	μA	1
	• @ $25\text{ }^{\circ}\text{C}$	—	0.1	μA	
I_{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	
I_{OZ}	Total Hi-Z (off-state) leakage current (all input pins)	—	4	μA	
R_{PU}	Internal pullup resistors	22	50	$\text{k}\Omega$	2
R_{PD}	Internal pulldown resistors	22	50	$\text{k}\Omega$	3

1. Tested by ganged leakage method

2. Measured at $V_{input} = V_{SS}$

3. Measured at $V_{input} = V_{DD}$

5.2.4 Power mode transition operating behaviors

All specifications except t_{POR} , and $V_{LLSx} \rightarrow \text{RUN}$ recovery times in the following table assume this clock configuration:

- CPU and system clocks = 50 MHz
- Bus clock = 50 MHz
- Flash clock = 25 MHz

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip.	—	300	μs	1
	• VLLS0 → RUN	—	130	μs	
	• VLLS1 → RUN	—	130	μs	
	• VLLS2 → RUN	—	70	μs	
	• VLLS3 → RUN	—	70	μs	
	• LLS → RUN	—	6	μs	
	• VLPS → RUN	—	5.2	μs	
	• STOP → RUN	—	5.2	μs	

1. Normal boot (FTFL_OPT[LPBOOT]=1)

5.2.5 Power consumption operating behaviors

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash	—	13.7	15.1	mA	2
		—	13.9	15.3	mA	
I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash	—	16.1	18.2	mA	3, 4
		—	16.3	17.7	mA	
		—	16.7	18.4	mA	
		—	16.7	18.4	mA	
I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	7.5	8.4	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	5.6	6.4	mA	5

Table continues on the next page...

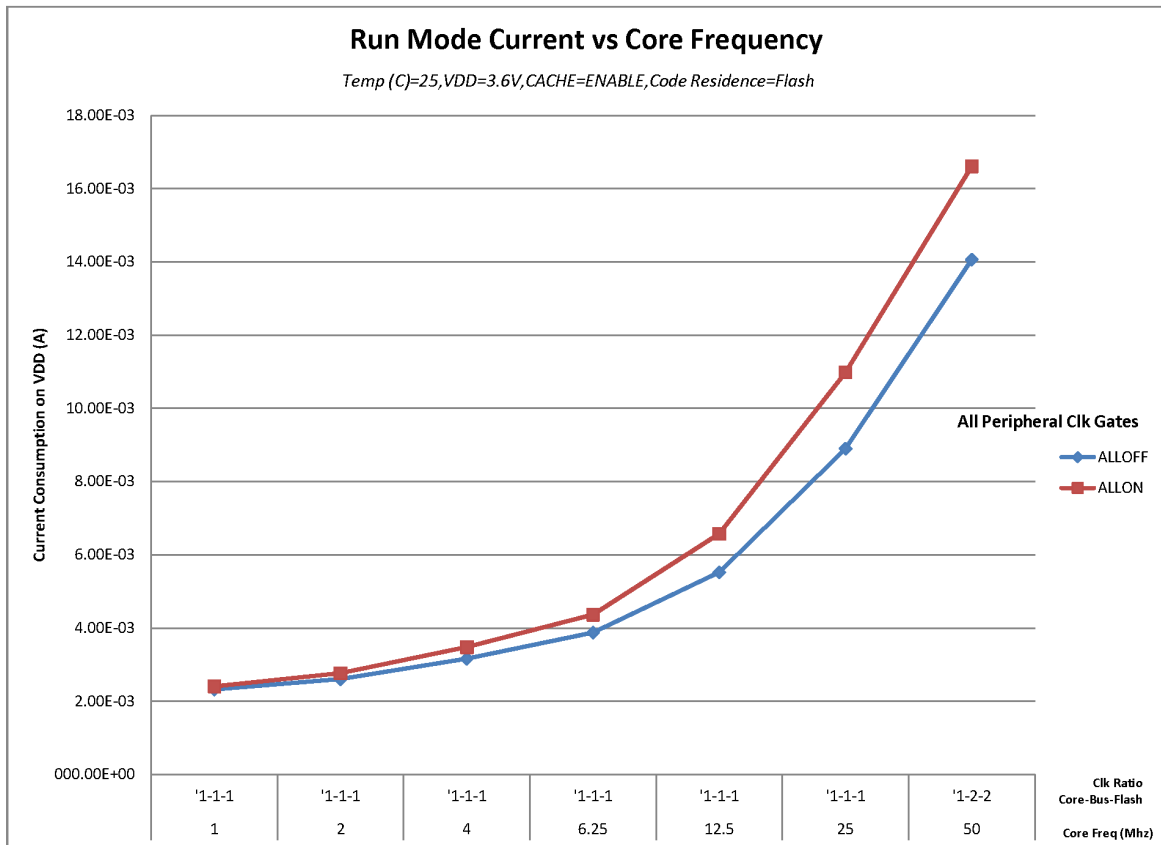


Figure 2. Run mode supply current vs. core frequency

emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

2. $V_{DD} = 3.3\text{ V}$, $T_A = 25\text{ }^{\circ}\text{C}$, $f_{OSC} = 12\text{ MHz}$ (crystal), $f_{SYS} = 48\text{ MHz}$, $f_{BUS} = 48\text{ MHz}$
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

5.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to <http://www.freescale.com>.
2. Perform a keyword search for “EMC design.”

5.2.8 Capacitance attributes

Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

5.3 Switching specifications

5.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
Normal run mode					
f_{SYS}	System and core clock	—	50	MHz	
f_{BUS}	Bus clock	—	50	MHz	
f_{FLASH}	Flash clock	—	25	MHz	
f_{LPTMR}	LPTMR clock	—	25	MHz	
VLPR mode ¹					
f_{SYS}	System and core clock	—	4	MHz	
f_{BUS}	Bus clock	—	4	MHz	
f_{FLASH}	Flash clock	—	1	MHz	
f_{ERCLK}	External reference clock	—	16	MHz	

Table continues on the next page...

Peripheral operating requirements and behaviors

Board type	Symbol	Description	64 MAPBGA	64 LQFP	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	90	53	°C/W	1,3
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	51	40	°C/W	,
—	$R_{\theta JB}$	Thermal resistance, junction to board	31	28	°C/W	5
—	$R_{\theta JC}$	Thermal resistance, junction to case	31	15	°C/W	6
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	6	3	°C/W	7

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)* with the single layer board horizontal. For the LQFP, the board meets the JESD51-3 specification. For the MAPBGA, the board meets the JESD51-9 specification.
3. Determined according to JEDEC Standard JESD51-6, *Integrated Circuits Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)* with the board horizontal.
5. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*. Board temperature is measured on the top surface of the board near the package.
6. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
7. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.

6 Peripheral operating requirements and behaviors

6.1 Core modules

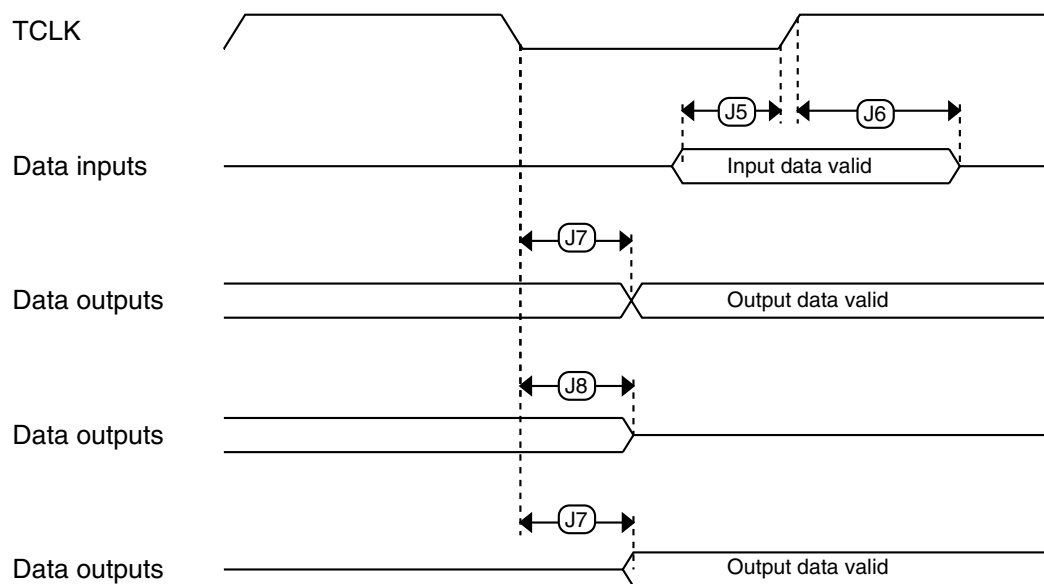


Figure 5. Boundary scan (JTAG) timing

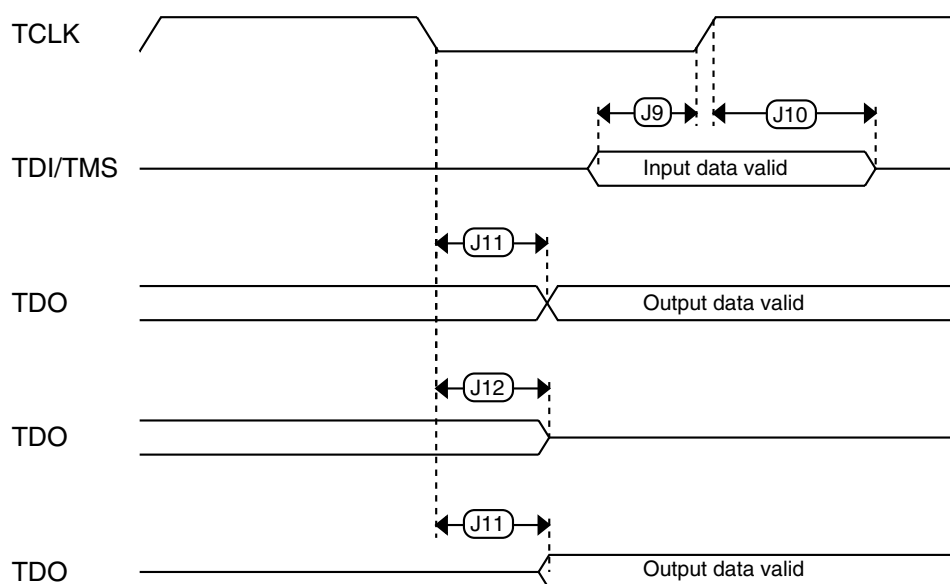


Figure 6. Test Access Port timing

Table 13. MCG specifications (continued)

Symbol	Description		Min.	Typ.	Max.	Unit	Notes
f _{fill_ref}	FLL reference frequency range		31.25	—	39.0625	kHz	
f _{dco}	DCO output frequency range	Low range (DRS=00) 640 × f _{fill_ref}	20	20.97	25	MHz	2, 3
		Mid range (DRS=01) 1280 × f _{fill_ref}	40	41.94	50	MHz	
		Mid-high range (DRS=10) 1920 × f _{fill_ref}	60	62.91	75	MHz	
		High range (DRS=11) 2560 × f _{fill_ref}	80	83.89	100	MHz	
f _{dco_t_DMx3} 2	DCO output frequency	Low range (DRS=00) 732 × f _{fill_ref}	—	23.99	—	MHz	4, 5
		Mid range (DRS=01) 1464 × f _{fill_ref}	—	47.97	—	MHz	
		Mid-high range (DRS=10) 2197 × f _{fill_ref}	—	71.99	—	MHz	
		High range (DRS=11) 2929 × f _{fill_ref}	—	95.98	—	MHz	
J _{cyc_fill}	FLL period jitter - f_{VCO} = 48 MHz - f_{VCO} = 98 MHz		— —	180 150	— —	ps	
t _{fill_acquire}	FLL target frequency acquisition time		—	—	1	ms	6
PLL							
f _{vco}	VCO operating frequency		48.0	—	100	MHz	
I _{pll}	PLL operating current PLL @ 96 MHz (f_{osc_hi_1} = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 48)		—	1060	—	μA	7
I _{pll}	PLL operating current PLL @ 48 MHz (f_{osc_hi_1} = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 24)		—	600	—	μA	7
f _{pll_ref}	PLL reference frequency range		2.0	—	4.0	MHz	
J _{cyc_pll}	PLL period jitter (RMS)						8
	- f_{vco} = 48 MHz - f_{vco} = 100 MHz		— —	120 50	— —	ps ps	

Table continues on the next page...

Table 14. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I _{DDOSC}	Supply current — high gain mode (HGO=1)					1
	• 32 kHz	—	25	—	μA	
	• 4 MHz	—	400	—	μA	
	• 8 MHz (RANGE=01)	—	500	—	μA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
C _x	EXTAL load capacitance	—	—	—		2, 3
C _y	XTAL load capacitance	—	—	—		2, 3
R _F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R _S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
V _{pp} ⁵	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V _{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V _{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C

2. See crystal or resonator manufacturer's recommendation

3. C_x,C_y can be provided by using either the integrated capacitors or by using external components.4. When low power mode is selected, R_F is integrated and must not be attached externally.

Table 16. 32kHz oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
C_{para}	Parasitical capacitance of EXTAL32 and XTAL32	—	5	7	pF
V_{pp} ¹	Peak-to-peak amplitude of oscillation	—	0.6	—	V

1. When a crystal is being used with the 32 kHz oscillator, the EXTAL32 and XTAL32 pins should only be connected to required oscillator components and must not be connected to any other devices.

6.3.3.2 32kHz oscillator frequency specifications

Table 17. 32kHz oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal	—	32.768	—	kHz	
t_{start}	Crystal start-up time	—	1000	—	ms	1
$f_{ec_extal32}$	Externally provided input clock frequency	—	32.768	—	kHz	2
$V_{ec_extal32}$	Externally provided input clock amplitude	700	—	V_{BAT}	mV	2, 3

1. Proper PC board layout procedures must be followed to achieve specifications.
2. This specification is for an externally supplied clock driven to EXTAL32 and does not apply to any other clock input. The oscillator remains enabled and XTAL32 must be left unconnected.
3. The parameter specified is a peak-to-peak value and V_{IH} and V_{IL} specifications do not apply. The voltage of the applied clock must be within the range of V_{SS} to V_{BAT} .

6.4 Memories and memory interfaces

6.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

6.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 18. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{hvp gm4}$	Longword Program high-voltage time	—	7.5	18	μs	
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversblk32k}$	Erase Block high-voltage time for 32 KB	—	52	452	ms	1
$t_{hversblk128k}$	Erase Block high-voltage time for 128 KB	—	52	452	ms	1

1. Maximum time based on expectations at cycling end-of-life.

6.4.1.2 Flash timing specifications — commands

Table 19. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1blk32k}$	Read 1s Block execution time	—	—	0.5	ms	
$t_{rd1blk128k}$	32 KB data flash 128 KB program flash	—	—	1.7	ms	
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	μs	1
t_{pgmchk}	Program Check execution time	—	—	45	μs	1
t_{rdsrc}	Read Resource execution time	—	—	30	μs	1
t_{pgm4}	Program Longword execution time	—	65	145	μs	
$t_{ersblk32k}$	Erase Flash Block execution time	—	55	465	ms	2
$t_{ersblk128k}$	32 KB data flash 128 KB program flash	—	61	495	ms	
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
$t_{pgmsec512}$	Program Section execution time	—	4.7	—	ms	
$t_{pgmsec1k}$	512 B flash 1 KB flash	—	9.3	—	ms	
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	
t_{rdonce}	Read Once execution time	—	—	25	μs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μs	
t_{ersall}	Erase All Blocks execution time	—	115	1000	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1
$t_{pgmpart32k}$	Program Partition for EEPROM execution time	—	70	—	ms	
$t_{setramff}$	Set FlexRAM Function execution time:	—	50	—	μs	
$t_{setram8k}$	- Control Code 0xFF 8 KB EEPROM backup	—	0.3	0.5	ms	
$t_{setram32k}$	32 KB EEPROM backup	—	0.7	1.0	ms	
Byte-write to FlexRAM for EEPROM operation						
$t_{eewr8bers}$	Byte-write to erased FlexRAM location execution time	—	175	260	μs	3
$t_{eewr8b8k}$	Byte-write to FlexRAM execution time:	—	340	1700	μs	
$t_{eewr8b16k}$	8 KB EEPROM backup 16 KB EEPROM backup	—	385	1800	μs	
$t_{eewr8b32k}$	32 KB EEPROM backup	—	475	2000	μs	

Table continues on the next page...

Table 21. NVM reliability specifications (continued)

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
$t_{\text{nvmretd1k}}$	Data retention after up to 1 K cycles	20	100	—	years	
n_{nvmcyed}	Cycling endurance	10 K	50 K	—	cycles	2
FlexRAM as EEPROM						
$t_{\text{nvmretee100}}$	Data retention up to 100% of write endurance	5	50	—	years	
$t_{\text{nvmretee10}}$	Data retention up to 10% of write endurance	20	100	—	years	
	Write endurance					3
$n_{\text{nvmwree16}}$	• EEPROM backup to FlexRAM ratio = 16	35 K	175 K	—	writes	
$n_{\text{nvmwree128}}$	• EEPROM backup to FlexRAM ratio = 128	315 K	1.6 M	—	writes	
$n_{\text{nvmwree512}}$	• EEPROM backup to FlexRAM ratio = 512	1.27 M	6.4 M	—	writes	
$n_{\text{nvmwree4k}}$	• EEPROM backup to FlexRAM ratio = 4096	10 M	50 M	—	writes	
$n_{\text{nvmwree8k}}$	• EEPROM backup to FlexRAM ratio = 8192	20 M	100 M	—	writes	

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at $-40^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$.
3. Write endurance represents the number of writes to each FlexRAM location at $-40^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$ influenced by the cycling endurance of the FlexNVM (same value as data flash) and the allocated EEPROM backup. Minimum and typical values assume all byte-writes to FlexRAM.

6.4.1.5 Write endurance to FlexRAM for EEPROM

When the FlexNVM partition code is not set to full data flash, the EEPROM data set size can be set to any of several non-zero values.

The bytes not assigned to data flash via the FlexNVM partition code are used by the flash memory module to obtain an effective endurance increase for the EEPROM data. The built-in EEPROM record management system raises the number of program/erase cycles that can be attained prior to device wear-out by cycling the EEPROM data through a larger EEPROM NVM storage space.

While different partitions of the FlexNVM are available, the intention is that a single choice for the FlexNVM partition code and EEPROM data set size is used throughout the entire lifetime of a given application. The EEPROM endurance equation and graph shown below assume that only one configuration is ever used.

$$\text{Writes_FlexRAM} = \frac{\text{EEPROM} - 2 \times \text{EEESIZE}}{\text{EEESIZE}} \times \text{Write_efficiency} \times n_{\text{nvmcyed}}$$

where

- Writes_FlexRAM — minimum number of writes to each FlexRAM location

Table 24. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
f_{ADACK}	ADC asynchronous clock source	- ADLPC=1, ADHSC=0 - ADLPC=1, ADHSC=1 - ADLPC=0, ADHSC=0 - ADLPC=0, ADHSC=1	1.2 3.0 2.4 4.4	2.4 4.0 5.2 6.2	3.9 7.3 6.1 9.5	MHz MHz MHz MHz	$t_{ADACK} = 1/f_{ADACK}$
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	12 bit modes <12 bit modes	— —	±4 ±1.4	±6.8 ±2.1	LSB ⁴	5
DNL	Differential non-linearity	12 bit modes <12 bit modes	— —	±0.7 ±0.2	-1.1 to +1.9 -0.3 to 0.5	LSB ⁴	5
INL	Integral non-linearity	12 bit modes <12 bit modes	— —	±1.0 ±0.5	-2.7 to +1.9 -0.7 to +0.5	LSB ⁴	5
E_{FS}	Full-scale error	12 bit modes <12 bit modes	— —	-4 -1.4	-5.4 -1.8	LSB ⁴	$V_{ADIN} = V_{DDA}$ 5
E_Q	Quantization error	16 bit modes ≤13 bit modes	— —	-1 to 0 —	— ±0.5	LSB ⁴	
ENOB	Effective number of bits	16 bit differential mode - Avg=32 - Avg=4 16 bit single-ended mode - Avg=32 - Avg=4	12.8 11.9 12.2 11.4	14.5 13.8 13.9 13.1	— — — —	bits bits bits bits	6
SINAD	Signal-to-noise plus distortion	See ENOB	$6.02 \times \text{ENOB} + 1.76$			dB	
THD	Total harmonic distortion	16 bit differential mode - Avg=32 16 bit single-ended mode - Avg=32	— —	-94 -85	— —	dB dB	7

Table continues on the next page...

Table 24. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
SFDR	Spurious free dynamic range	16 bit differential mode • Avg=32	82	95	—	dB	7
		16 bit single-ended mode • Avg=32	78	90	—	dB	
E _{IL}	Input leakage error		$I_{in} \times R_{AS}$			mV	I_{in} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	−40°C to 105°C	—	1.715	—	mV/°C	
V _{TEMP25}	Temp sensor voltage	25°C	—	719	—	mV	

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume $V_{DDA} = 3.0$ V, Temp = 25°C, $f_{ADCK} = 2.0$ MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and the ADLPC bit (low power). For lowest power operation the ADLPC bit should be set, the HSC bit should be clear with 1MHz ADC conversion clock speed.
4. $1 \text{ LSB} = (V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock <16MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock <12MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock <12MHz.

6.6.2 CMP and 6-bit DAC electrical specifications

Table 25. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	μ A
$I_{DDL S}$	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	μ A
V_{AIN}	Analog input voltage	$V_{SS} - 0.3$	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis ¹				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOH}	Output high	$V_{DD} - 0.5$	—	—	V
V_{CMPOI}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay ²	—	—	40	μ s
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μ A
INL	6-bit DAC integral non-linearity	−0.5	—	0.5	LSB ³
DNL	6-bit DAC differential non-linearity	−0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to $V_{DD}-0.6V$.

2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.

3. 1 LSB = $V_{reference}/64$

6.8.1 DSPI switching specifications (limited voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provide DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 30. Master mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	—	25	MHz	
DS1	DSPI_SCK output cycle time	$2 \times t_{\text{BUS}}$	—	ns	
DS2	DSPI_SCK output high/low time	$(t_{\text{SCK}}/2) - 2$	$(t_{\text{SCK}}/2) + 2$	ns	
DS3	DSPI_PCS _n valid to DSPI_SCK delay	$(t_{\text{BUS}} \times 2) - 2$	—	ns	1
DS4	DSPI_SCK to DSPI_PCS _n invalid delay	$(t_{\text{BUS}} \times 2) - 2$	—	ns	2
DS5	DSPI_SCK to DSPI_SOUT valid	—	8	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	0	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	14	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].

2. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

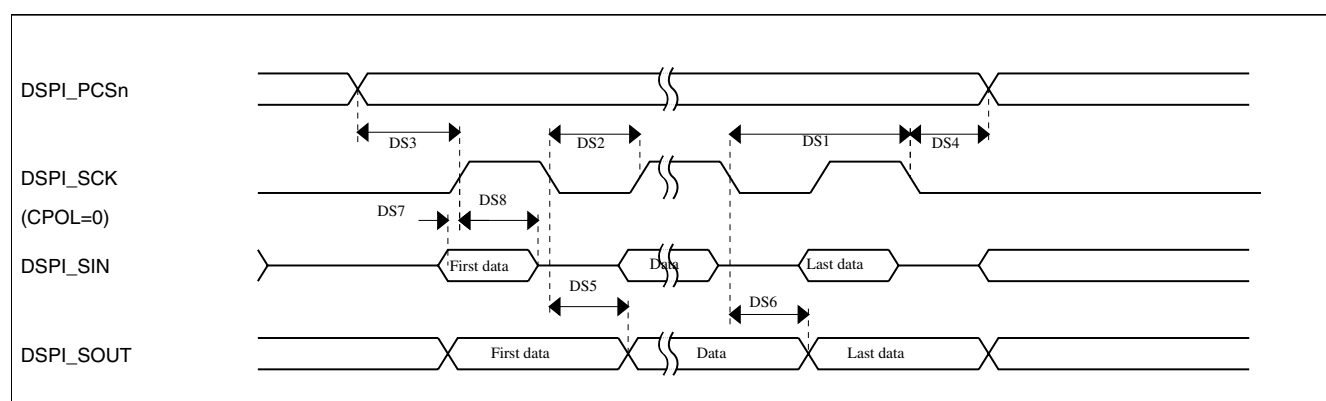


Figure 15. DSPI classic SPI timing — master mode

Table 31. Slave mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
	Frequency of operation		12.5	MHz

Table continues on the next page...

6.8.5.1 Normal Run, Wait and Stop mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in Normal Run, Wait and Stop modes.

Table 34. I2S/SAI master mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	25	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

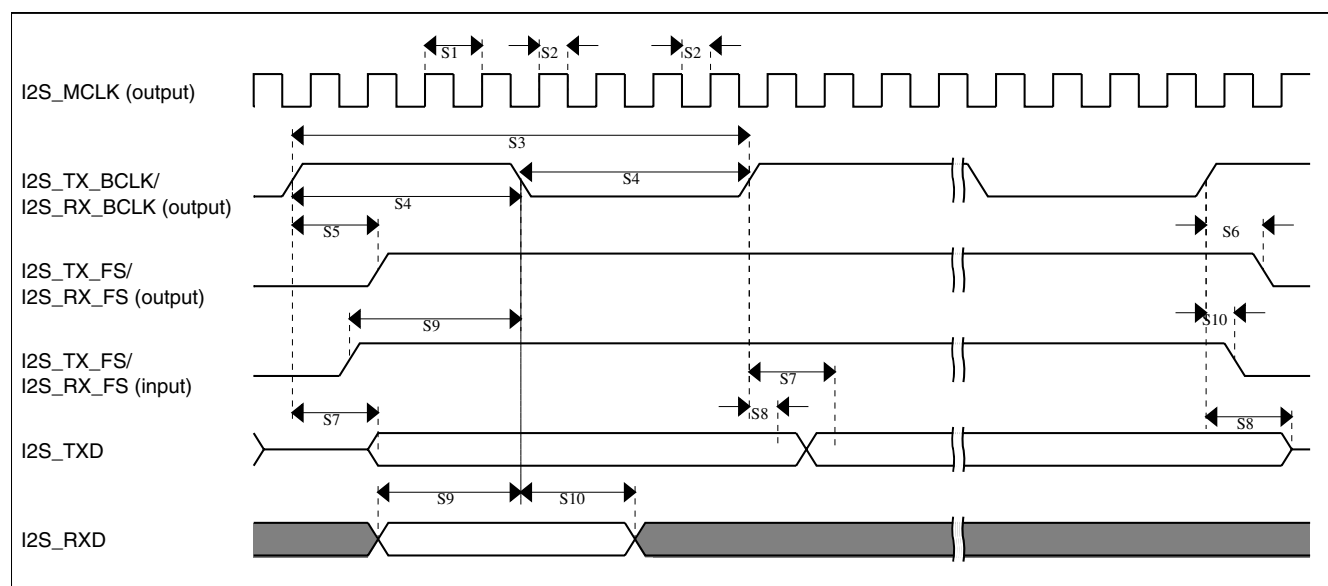


Figure 19. I2S/SAI timing — master modes